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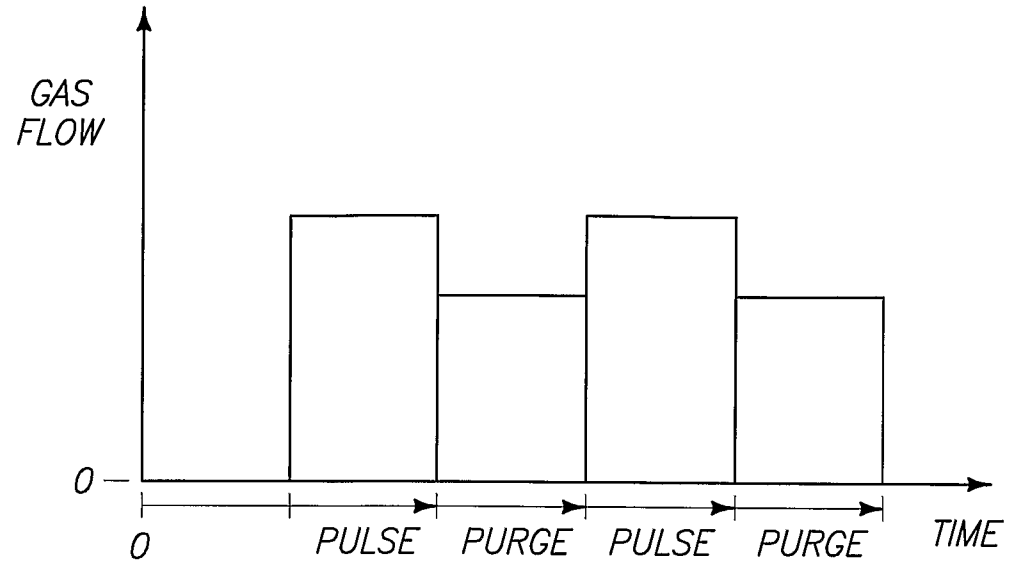
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(54) Title: METHODS FOR DEPOSITION OF SEMICONDUCTOR MATERIAL



(57) Abstract: The invention includes a method for selective deposition of semiconductor material. A substrate is placed within a reaction chamber. The substrate comprises a first surface and a second surface. The first and second surfaces are exposed to a semiconductor material precursor under conditions in which growth of semiconductor material from the precursor comprises a lag phase prior to a growth phase, and under which it takes longer for the growth phase to initiate on the second surface than on the first surface. The exposure of the first and second surfaces is conducted for a time sufficient for the growth phase to occur on the first surface, but not long enough for the growth phase to occur on the second surface.

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